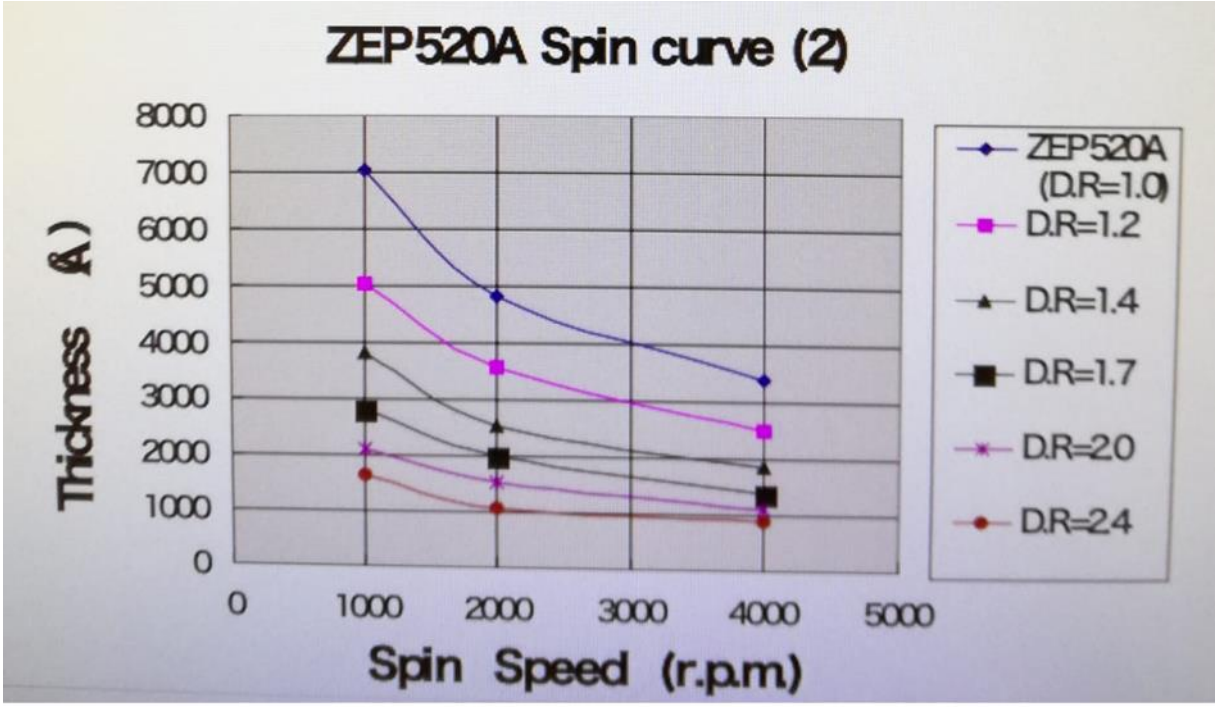
ZEP520A (D.R=1.0)

Tone	Positive
Spincoat	1000-4000rpm: 700nm-350nm (see below)
Prebake	180°C, 10 minutes on hotplate
Exposure	D=180uC/cm2
Development (two possibilities)	pentylacetate for 90s, rinse: MIBK:IPA=9:1 for 30s, followed by 30s IPA
OR	20-22s in oxylene, Rinse: IPA:MIBK=3 for 15s, followed by 30s IPA



D.R={Resist+Solvent}/Resist (Weight Ratio)

<u>Etchresistance</u>

In the table below you can find the etchrates for different plasmas:

	Etchrate gas 1 [nm/min]	Etchrate gas 2 [nm/min]	Etchrate gas 3 [nm/min]	Etchrate gas 4 [nm/min]
AR-P 6200	66	93	29	54
PMMA	104	133	44	71
ZEP520A	64	86	27.5	48

Gas 1: etcher F2, 20sccm O2, 40W, lowest pressure, bias -541V à -648V
Gas 2: etcher F2, 12.5sccm SF6, 10sccm He, 2.5sccm O2, 10µbar, 40W, bias -210V
Gas 3: etcher F1, 50sccm CHF3, 2.5sscm O2, 8.6µbar, 50W, bias -442V
Gas 4: etcher F1, 50sccm CHF3, 2.5sccm O2, 50µbar, 100W, bias -613V